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April 1, 2003

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# HM62W16258B Series

4 M SRAM (256-kword  $\times$  16-bit)



ADE-203-976B (Z)

Rev. 2.0

Oct. 14, 1999

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## Description

The Hitachi HM62W16258B Series is 4-Mbit static RAM organized 262,144-word  $\times$  16-bit. HM62W16258B Series has realized higher density, higher performance and low power consumption by employing Hi-CMOS process technology. It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is packaged in standard 44-pin plastic TSOPII.

## Features

- Single 3.3 V supply:  $3.3\text{ V} \pm 0.3\text{ V}$
- Fast access time: 55 ns/70 ns (max)
- Power dissipation:
  - Active: 9.9 mW (typ)
  - Standby:  $3.3\text{ }\mu\text{W}$  (typ)
- Completely static memory.
  - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
  - Three state output
- Battery backup operation.

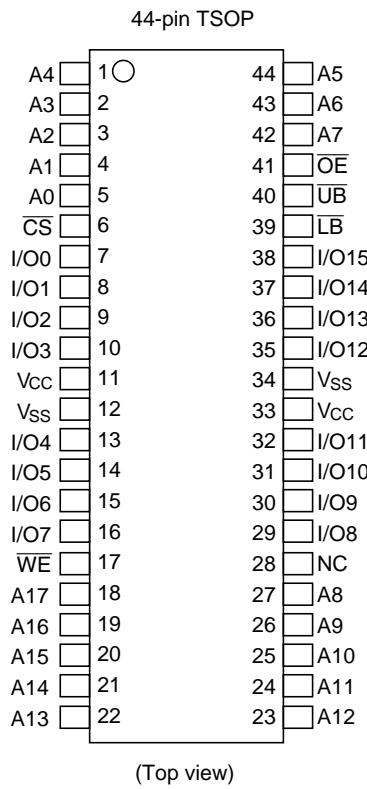
## HM62W16258B Series

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### Ordering Information

Type No.	Access time	Package
HM62W16258BLTT-5	55 ns	400-mil 44-pin plastic TSOPII (normal-bend type) (TTP-44DB)
HM62W16258BLTT-7	70 ns	
HM62W16258BLTT-5SL	55 ns	
HM62W16258BLTT-7SL	70 ns	

## Pin Arrangement

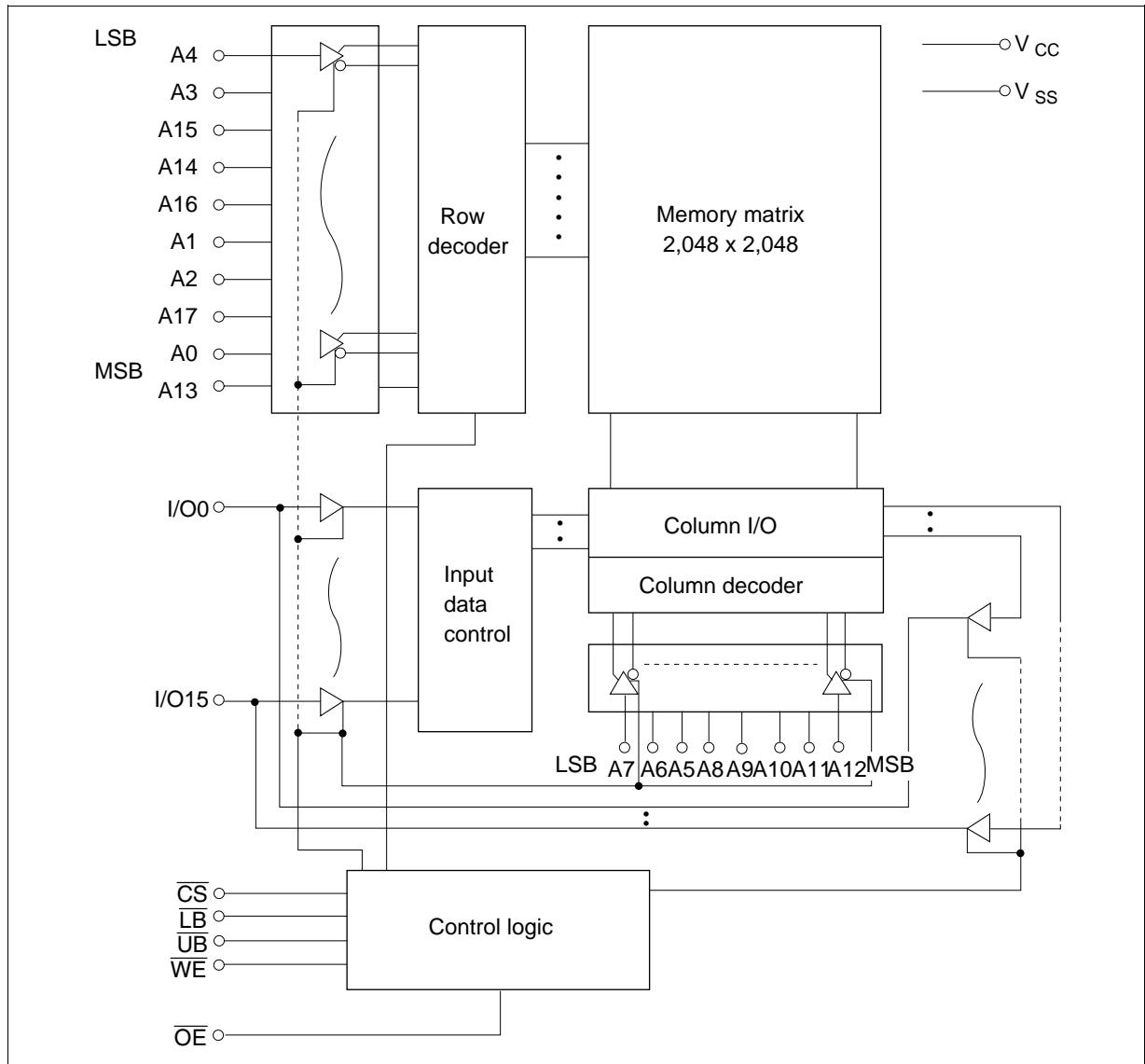


(Top view)

## Pin Description

Pin name	Function
A0 to A17	Address input
I/O0 to I/O15	Data input/output
CS	Chip select
WE	Write enable
OE	Output enable
LB	Lower byte select
UB	Upper byte select
V <sub>cc</sub>	Power supply
V <sub>ss</sub>	Ground
NC	No connection

## Block Diagram



## Operation Table

CS	WE	OE	UB	LB	I/O0 to I/O7	I/O8 to I/O15	Operation
H	x	x	x	x	High-Z	High-Z	Standby
x	x	x	H	H	High-Z	High-Z	Standby
L	H	L	L	L	Dout	Dout	Read
L	H	L	H	L	Dout	High-Z	Lower byte read
L	H	L	L	H	High-Z	Dout	Upper byte read
L	L	x	L	L	Din	Din	write
L	L	x	H	L	Din	High-Z	Lower byte write
L	L	x	L	H	High-Z	Din	Upper byte write
L	H	H	x	x	High-Z	High-Z	Output disable

Note: H:  $V_{IH}$ , L:  $V_{IL}$ , x:  $V_{IH}$  or  $V_{IL}$

## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to $V_{SS}$	$V_{CC}$	-0.5 to + 4.6	V
Terminal voltage on any pin relative to $V_{SS}$	$V_T$	-0.5 <sup>*1</sup> to $V_{CC} + 0.3$ <sup>*2</sup>	V
Power dissipation	$P_T$	1.0	W
Storage temperature range	$T_{STG}$	-55 to +125	°C
Storage temperature range under bias	$T_{BIA}$	-10 to +85	°C

Notes: 1.  $V_T$  min: -3.0 V for pulse half-width  $\leq 30$  ns.

2. Maximum voltage is +4.6 V.

## DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	$V_{CC}$	3.0	3.3	3.6	V	
	$V_{SS}$	0	0	0	V	
Input high voltage	$V_{IH}$	2.0	—	$V_{CC} + 0.3$	V	
Input low voltage	$V_{IL}$	-0.3	—	0.8	V	1
Ambient temperature range	$T_a$	0	—	70	°C	

Note: 1.  $V_{IL}$  min: -3.0 V for pulse half-width  $\leq 30$  ns.

## DC Characteristics

Parameter	Symbol	Min	Typ <sup>*1</sup>	Max	Unit	Test conditions
Input leakage current	$ I_{IL} $	—	—	1	$\mu A$	$V_{in} = V_{ss}$ to $V_{cc}$
Output leakage current	$ I_{LO} $	—	—	1	$\mu A$	$\overline{CS} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$ , or $\overline{LB} = \overline{UB} = V_{IH}$ , $V_{IO} = V_{ss}$ to $V_{cc}$
Operating current	$I_{CC}$	—	—	20	mA	$\overline{CS} = V_{IL}$ , Others = $V_{IH}/V_{IL}$ , $I_{IO} = 0$ mA
Average operating current	HM62W16258B-5	$I_{CC1}$	—	80	mA	Min. cycle, duty = 100%, $I_{IO} = 0$ mA, $\overline{CS} = V_{IL}$ , Others = $V_{IH}/V_{IL}$
HM62W16258B-7		$I_{CC1}$	—	70	mA	
		$I_{CC2}$	—	3	15	mA
						Cycle time = 1 $\mu s$ , duty = 100%, $I_{IO} = 0$ mA, $\overline{CS} \leq 0.2$ V, $V_{IH} \geq V_{cc} - 0.2$ V, $V_{IL} \leq 0.2$ V
Standby current	$I_{SB}$	—	—	0.3	mA	$\overline{CS} = V_{IH}$
Standby current	$I_{SB1}^{*2}$	—	1	40	$\mu A$	$0 \text{ V} \leq V_{in}$ $\overline{CS} \geq V_{cc} - 0.2$ V
	$I_{SB1}^{*3}$	—	1	20	$\mu A$	
Output high voltage	$V_{OH}$	2.4	—	—	V	$I_{OH} = -1$ mA
		$V_{cc} - 0.2$	—	—	V	$I_{OH} = -100$ $\mu A$
Output low voltage	$V_{OL}$	—	—	0.4	V	$I_{OL} = 2$ mA
		—	—	0.2	V	$I_{OL} = 100$ $\mu A$

Notes: 1. Typical values are at  $V_{cc} = 3.0$  V,  $Ta = +25^\circ C$  and not guaranteed.

2. This characteristic is guaranteed only for L-version.

3. This characteristic is guaranteed only for L-SL version.

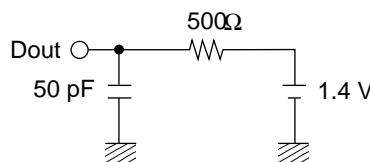
## Capacitance ( $Ta = +25^\circ C$ , $f = 1.0$ MHz)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	Note
Input capacitance	$C_{in}$	—	—	8	pF	$V_{in} = 0$ V	1
Input/output capacitance	$C_{IO}$	—	—	10	pF	$V_{IO} = 0$ V	1

Note: 1. This parameter is sampled and not 100% tested.

**AC Characteristics** (Ta = 0 to +70°C, V<sub>CC</sub> = 3.3 V ± 0.3 V, unless otherwise noted.)**Test Conditions**

- Input pulse levels: V<sub>IL</sub> = 0.4 V, V<sub>IH</sub> = 2.4 V
- Input rise and fall time: 5 ns
- Input timing reference levels: 1.4 V
- Output timing reference levels: 1.4 V/1.4 V (HM62W16258B-5)  
: 2.0 V/0.8 V (HM62W16258B-7)
- Output load (Including scope and jig)

**Read Cycle****HM62W16258B**

Parameter	Symbol	HM62W16258B		Unit	Notes
		-5	-7		
Read cycle time	t <sub>RC</sub>	55	—	70	—
Address access time	t <sub>AA</sub>	—	55	—	70
Chip select access time	t <sub>ACS</sub>	—	55	—	70
Output enable to output valid	t <sub>OE</sub>	—	35	—	40
Output hold from address change	t <sub>OH</sub>	10	—	10	—
LB, UB access time	t <sub>BA</sub>	—	55	—	70
Chip select to output in low-Z	t <sub>CLZ</sub>	10	—	10	—
LB, UB enable to low-z	t <sub>BLZ</sub>	5	—	5	—
Output enable to output in low-Z	t <sub>OLZ</sub>	5	—	5	—
Chip deselect to output in high-Z	t <sub>CHZ</sub>	0	20	0	25
LB, UB disable to high-Z	t <sub>BHZ</sub>	0	20	0	25
Output disable to output in high-Z	t <sub>OHZ</sub>	0	20	0	25

## HM62W16258B Series

## Write Cycle

HM62W16258B

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-5 -7

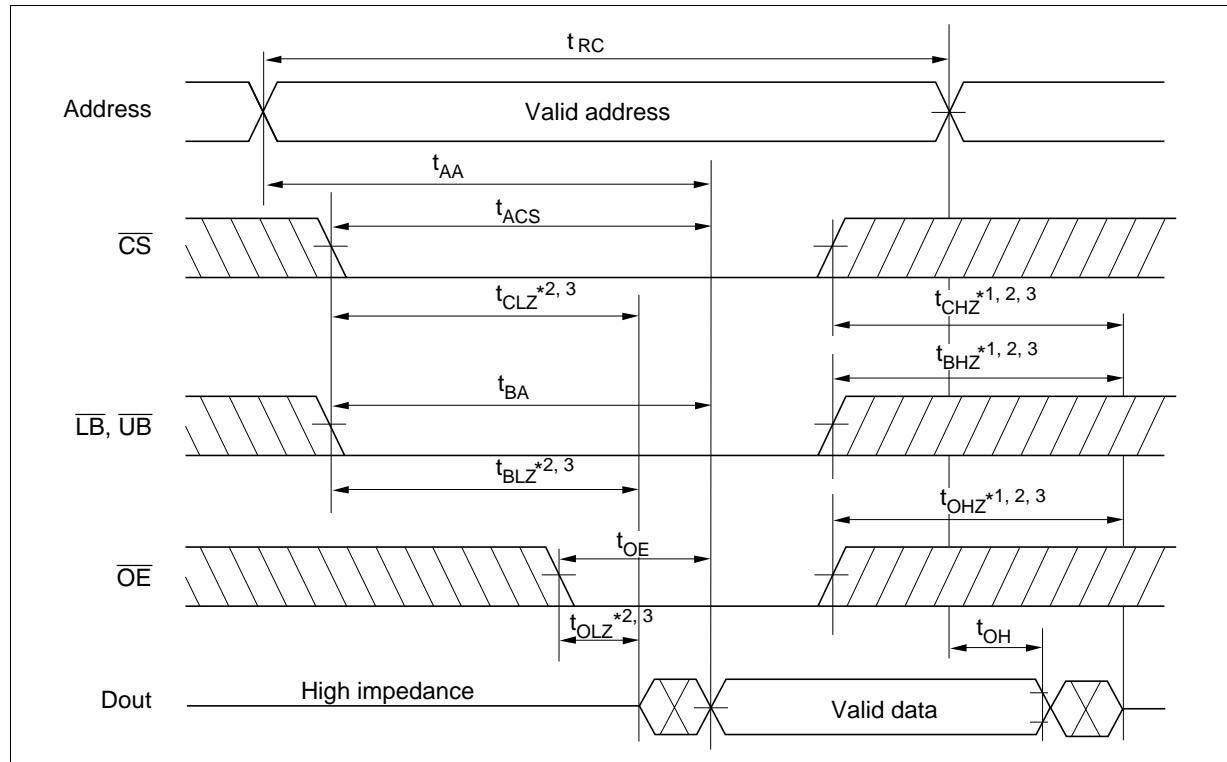
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	$t_{WC}$	55	—	70	—	ns	
Address valid to end of write	$t_{AW}$	50	—	60	—	ns	
Chip selection to end of write	$t_{CW}$	50	—	60	—	ns	5
Write pulse width	$t_{WP}$	40	—	50	—	ns	4
LB, UB valid to end of write	$t_{BW}$	50	—	55	—	ns	
Address setup time	$t_{AS}$	0	—	0	—	ns	6
Write recovery time	$t_{WR}$	0	—	0	—	ns	7
Data to write time overlap	$t_{DW}$	25	—	30	—	ns	
Data hold from write time	$t_{DH}$	0	—	0	—	ns	
Output active from end of write	$t_{OW}$	5	—	5	—	ns	2
Output disable to output in High-Z	$t_{OHZ}$	0	20	0	25	ns	1, 2
Write to output in high-Z	$t_{WHZ}$	0	20	0	25	ns	1, 2

Notes: 1.  $t_{CHZ}$ ,  $t_{OHZ}$ ,  $t_{WHZ}$  and  $t_{BHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

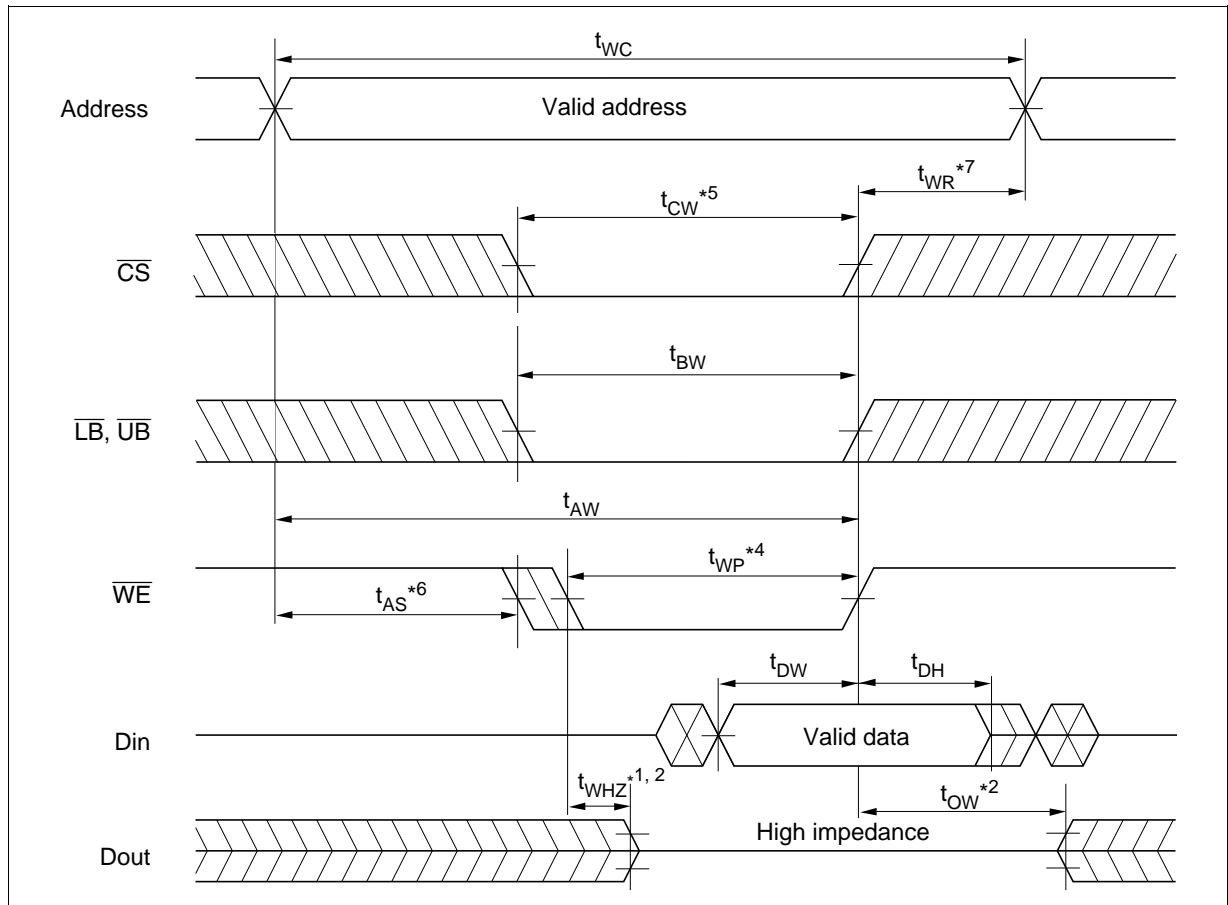
2. This parameter is sampled and not 100% tested.
3. At any given temperature and voltage condition,  $t_{HZ}$  max is less than  $t_{LZ}$  min both for a given device and from device to device.
4. A write occurs during the overlap of a low  $\overline{CS}$ , a low  $\overline{WE}$  and a low  $\overline{LB}$  or a low  $\overline{UB}$ . A write begins at the latest transition among  $\overline{CS}$  going low,  $\overline{WE}$  going low and  $\overline{LB}$  going low or  $\overline{UB}$  going low. A write ends at the earliest transition among  $\overline{CS}$  going high,  $\overline{WE}$  going high and  $\overline{LB}$  going high or  $\overline{UB}$  going high.  $t_{WP}$  is measured from the beginning of write to the end of write.
5.  $t_{CW}$  is measured from the later of  $\overline{CS}$  going low to the end of write.
6.  $t_{AS}$  is measured from the address valid to the beginning of write.
7.  $t_{WR}$  is measured from the earliest of  $\overline{CS}$  or  $\overline{WE}$  going high to the end of write cycle.

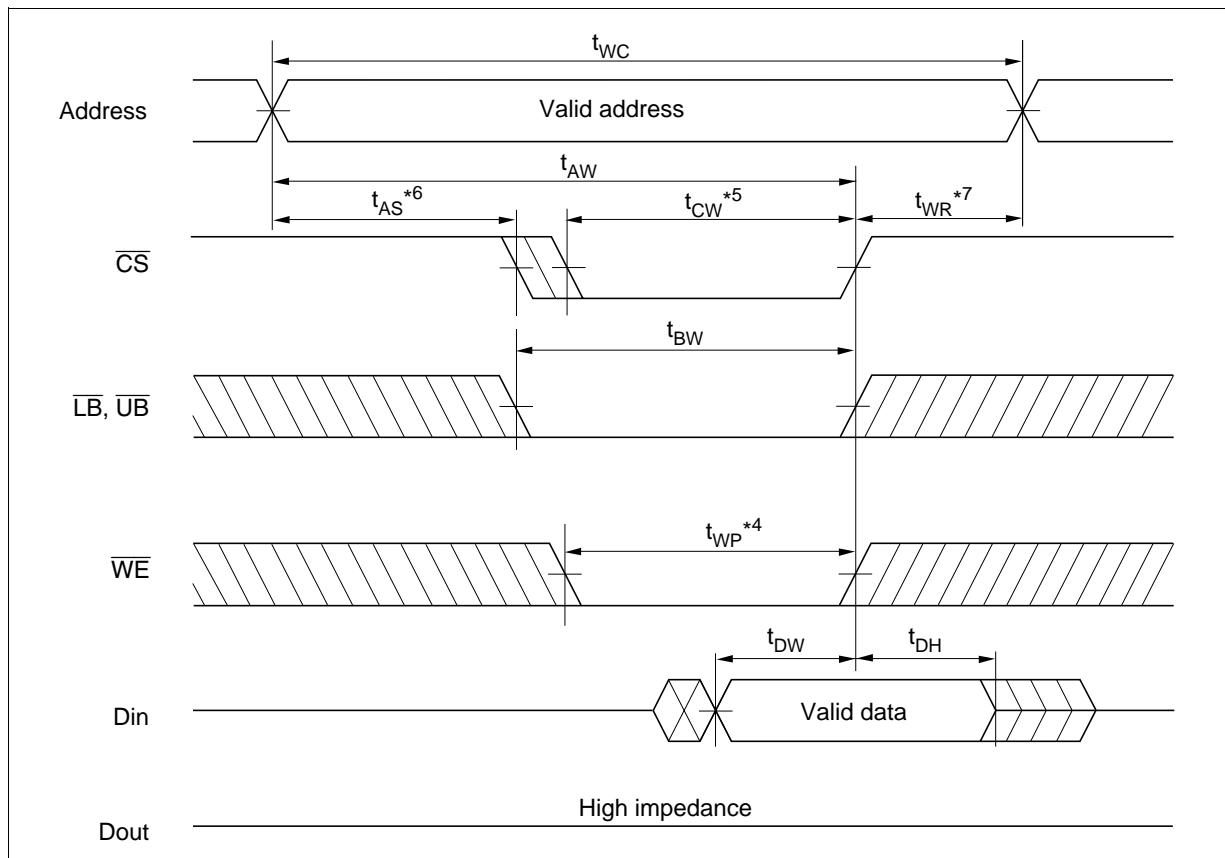
## Timing Waveform

## Read Cycle

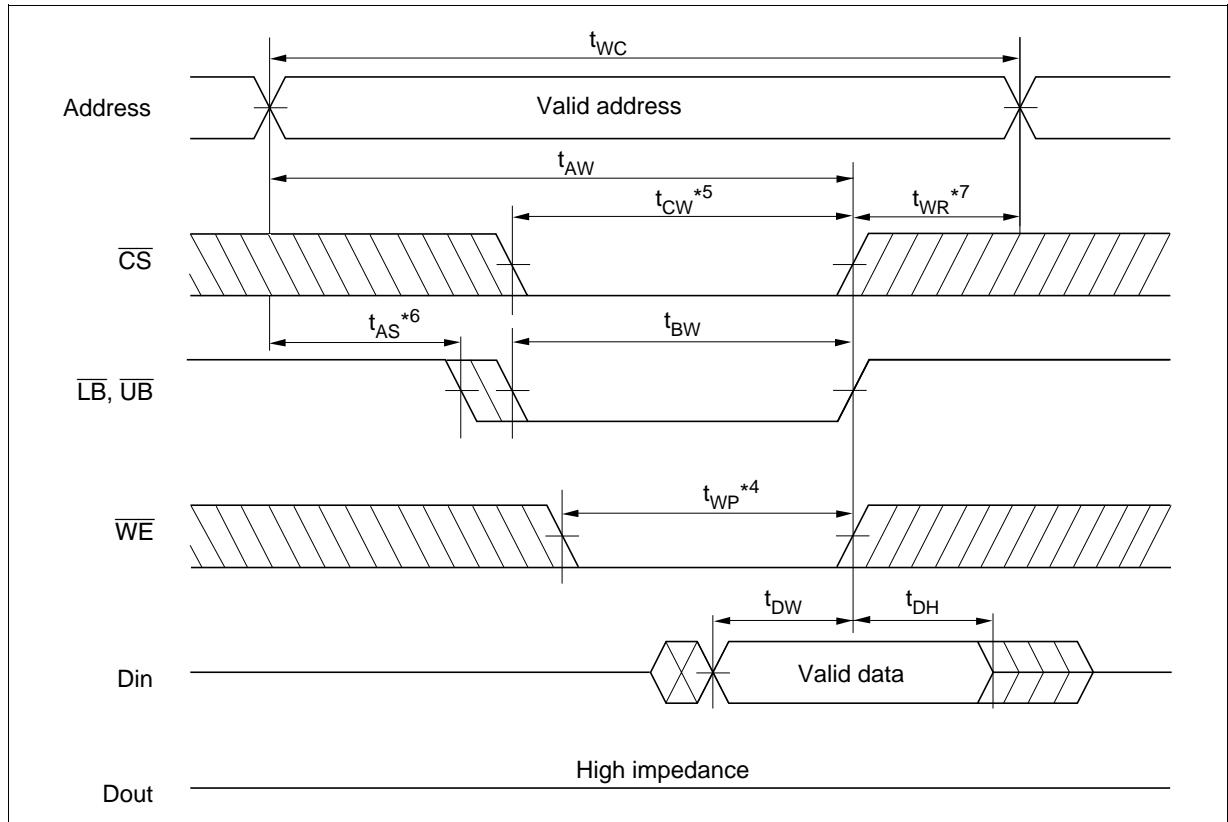


## Write Cycle (1) ( $\overline{\text{WE}}$ Clock)



Write Cycle (2) ( $\overline{\text{CS}}$  Clock,  $\overline{\text{OE}} = \text{V}_{\text{IH}}$ )

## Write Cycle (3) ( $\overline{LB}$ , $\overline{UB}$ Clock, $\overline{OE} = V_{IH}$ )



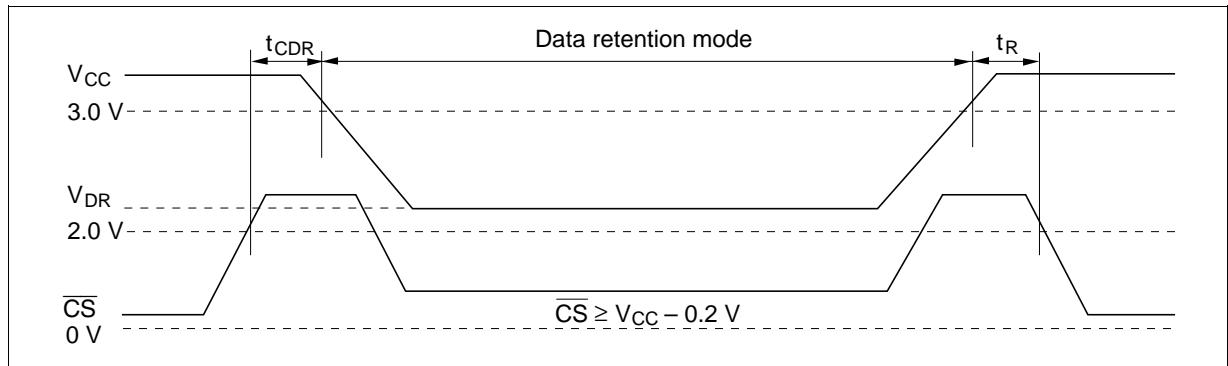
Low  $V_{CC}$  Data Retention Characteristics ( $T_a = 0$  to  $+70^\circ C$ )

Parameter	Symbol	Min	Typ <sup>*4</sup>	Max	Unit	Test conditions <sup>*3</sup>
$V_{CC}$ for data retention	$V_{DR}$	2.0	—	—	V	$V_{in} \geq 0V$ (1) $\overline{CS} \geq V_{CC} - 0.2V$ or (2) $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2V$ $\overline{CS} \leq 0.2V$
Data retention current	$I_{CCDR}^{*1}$	—	0.8	20	$\mu A$	$V_{CC} = 3.0V$ , $V_{in} \geq 0V$ (1) $\overline{CS} \geq V_{CC} - 0.2V$ or (2) $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2V$ $\overline{CS} \leq 0.2V$
	$I_{CCDR}^{*2}$	—	0.8	10	$\mu A$	
Chip deselect to data retention time	$t_{CDR}$	0	—	—	ns	See retention waveform
Operation recovery time	$t_R$		$t_{RC}^{*5}$	—	—	ns

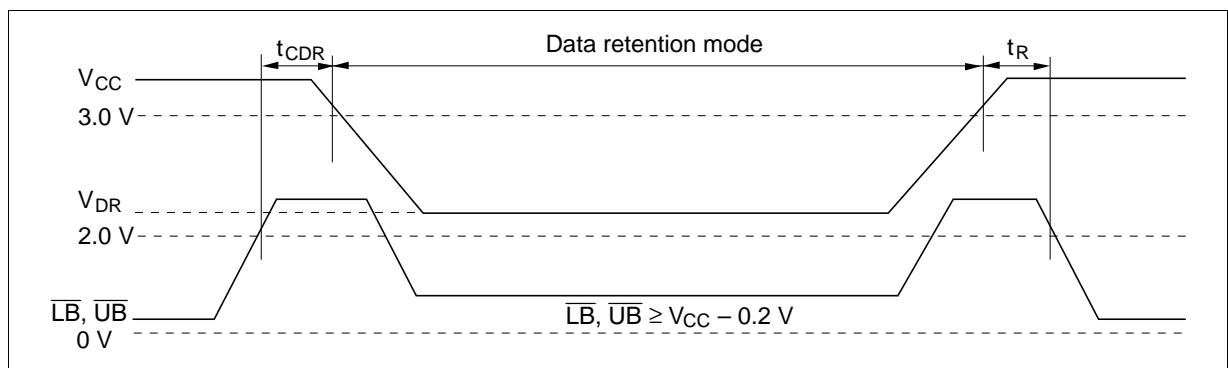
Notes:

1. This characteristic is guaranteed only for L-version, 10  $\mu A$  max. at  $T_a = 0$  to  $+40^\circ C$ .
2. This characteristic is guaranteed only for L-SL version, 5  $\mu A$  max. at  $T_a = 0$  to  $+40^\circ C$ .
3.  $\overline{CS}$  controls address buffer,  $\overline{WE}$  buffer,  $\overline{OE}$  buffer,  $\overline{LB}$ ,  $\overline{UB}$  buffer and Din buffer. If  $\overline{CS}$  controls data retention mode,  $V_{in}$  levels (address,  $\overline{WE}$ ,  $\overline{OE}$ ,  $\overline{LB}$ ,  $\overline{UB}$ , I/O) can be in the high impedance state. If  $\overline{LB}$ ,  $\overline{UB}$  controls data retention mode,  $\overline{LB}$ ,  $\overline{UB}$  must be  $\overline{LB} = \overline{UB} \geq V_{CC} - 0.2V$ ,  $\overline{CS}$  must be  $CS \leq 0.2V$ . The other input levels (address,  $WE$ ,  $OE$ , I/O) can be in the high impedance state.
4. Typical values are at  $V_{CC} = 3.0V$ ,  $T_a = +25^\circ C$  and not guaranteed.
5.  $t_{RC} =$  read cycle time.

## Low $V_{CC}$ Data Retention Timing Waveform (1) ( $\overline{CS}$ Controlled)



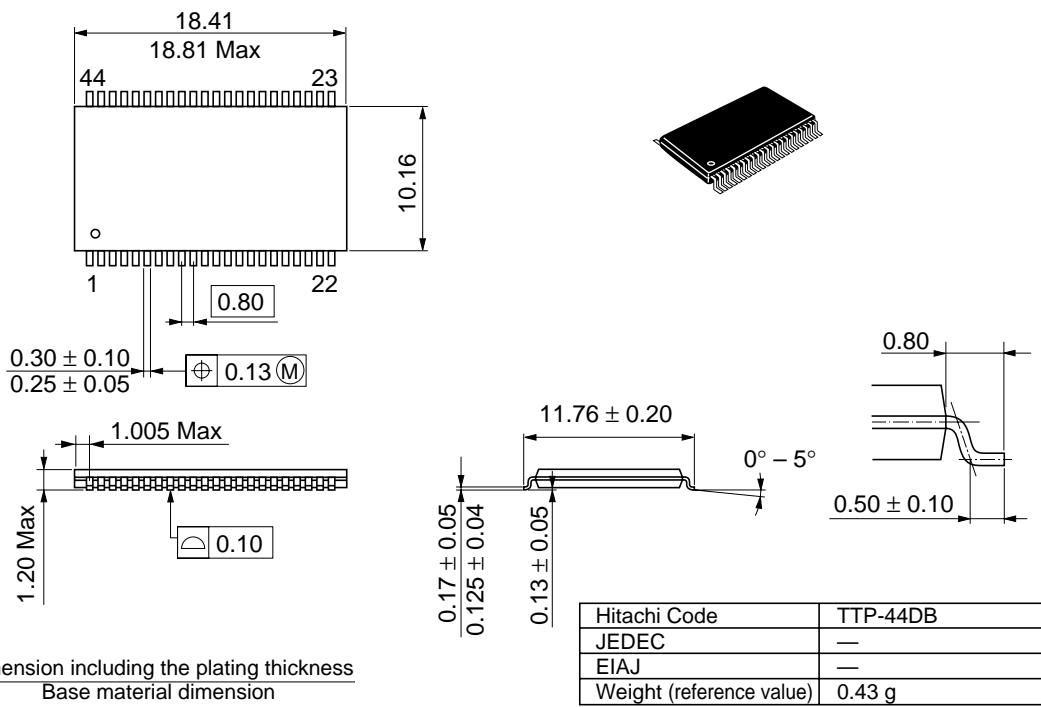
## Low $V_{CC}$ Data Retention Timing Waveform (2) ( $\overline{LB}$ , $\overline{UB}$ Controlled)



## Package Dimensions

## HM62W16258BLTT Series (TTP-44DB)

Unit: mm



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